

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

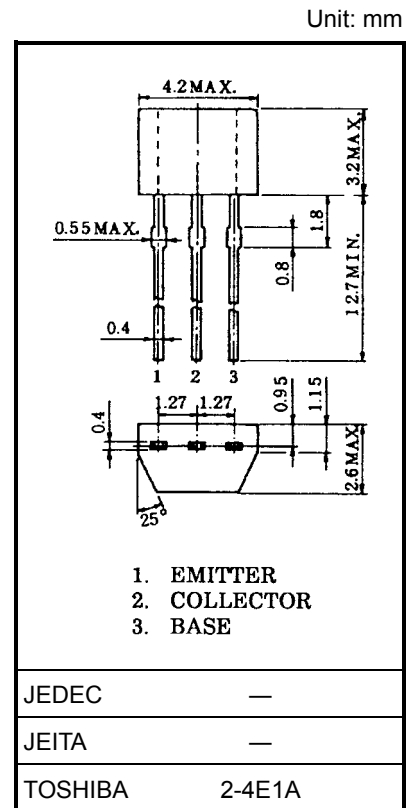
# 2SA1049

## Audio Frequency Amplifier Applications

- Small package.
- High breakdown voltage:  $V_{CEO} = -120\text{ V}$
- High  $h_{FE}$ :  $h_{FE} = 200\sim700$
- Excellent  $h_{FE}$  linearity:  $h_{FE}(I_C = -0.1\text{ mA})/h_{FE}(I_C = -2\text{ mA}) = 0.95$  (typ.)
- Low noise:  $NF = 1\text{ dB}$  (typ.),  $10\text{ dB}$  (max)
- Complementary to 2SC2459.

## Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-120	V
Collector-emitter voltage	$V_{CEO}$	-120	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-100	mA
Base current	$I_B$	-20	mA
Collector power dissipation	$P_C$	200	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55~125	$^\circ\text{C}$



Weight: 0.13 g (typ.)

## Electrical Characteristics ( $T_a = 25^\circ\text{C}$ )

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	$I_{CBO}$	$V_{CB} = -120\text{ V}, I_E = 0$	—	—	-0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5\text{ V}, I_C = 0$	—	—	-0.1	$\mu\text{A}$
DC current gain	$h_{FE}$ (Note)	$V_{CE} = -6\text{ V}, I_C = -2\text{ mA}$	200	—	700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10\text{ mA}, I_B = -1\text{ mA}$	—	—	-0.3	V
Transition frequency	$f_T$	$V_{CE} = -6\text{ V}, I_C = -1\text{ mA}$	—	100	—	MHz
Collector output capacitance	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	4	—	pF
Noise figure	NF	$V_{CE} = -6\text{ V}, I_C = -0.1\text{ mA}$ $f = 1\text{ kHz}, R_G = 10\text{ k}\Omega$	—	1.0	10	dB

Note:  $h_{FE}$  classification GR: 200~400, BL: 350~700

